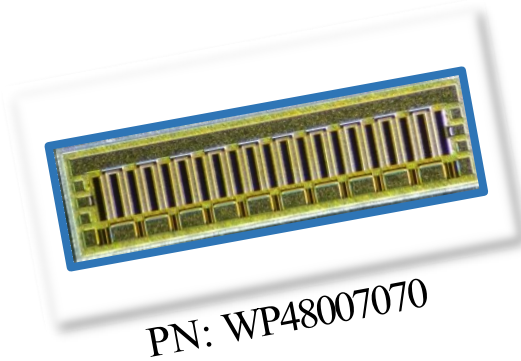




WP48007070

70W, 48V GaN HEMT Die



The WP48007070 is a 70W gallium nitride (GaN) High Electron Mobility Transistor (HEMT). This GaN HEMT is a wideband transistor optimized for 5.8GHz operation in a user-friendly device for high bandwidth applications. Gallium nitride (GaN) HEMT is a device optimized for 5G. GaN HEMT resistance is only 1/10 that of silicon transistors, making it capable of switching frequencies faster for greater energy efficiency.

Features

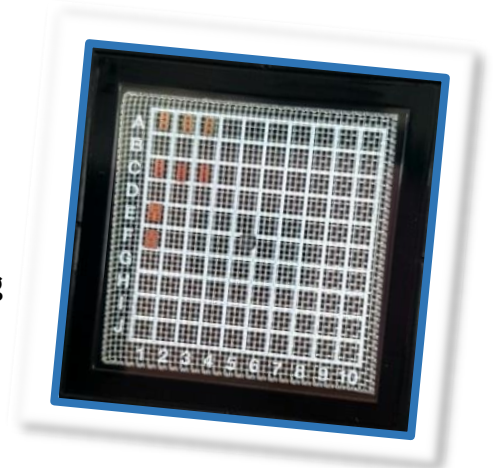
- Up to 8 GHz Operation
- 14.0 dB Typical Small Signal Gain @ 3.5 GHz
- 70 W Typical Psat @5.8GHz
- 48V Operation
- High Breakdown Voltage
- High Breakdown Voltage
- High Efficiency
- Reliability Monitoring Supporting

Applications

- U/VHF Amplifiers
- Broadband Amplifiers
- Base Station Communications
- Drone, UAV
- WiMAX, LTE, WCDMA, GSM
- WPT, V2X
- Radar application

Packaging Information

- Bare die are shipped in Wafer-level with Expander Ring or Gel-Pak® containers.
- Possible UV Curing for Wafer-level with dicing saw



Absolute Maximum Ratings (not simultaneous) at 25 °C

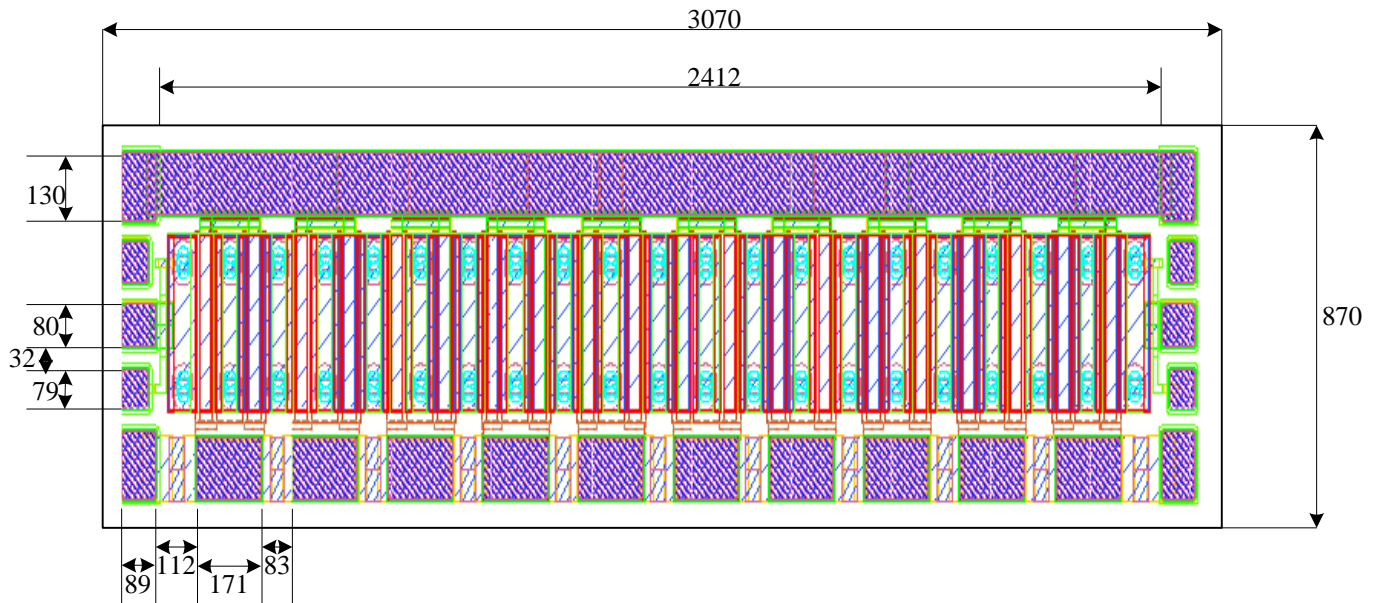
Parameter	Parameter	Typical Value	Units	Conditions
Threshold voltage @ Id=1mA/mm, Vd=10V	V _{to}	-3.4	V	25°C
Breakdown voltage @ Id=1mA/mm	V _{DG}	160	V	25°C
Drain-source current, Id @ Vd=10V, Vg=0	I _{dss}	800	mA/mm	25°C
Operating Junction Temperature	T _J	225	°C	
Storage Temperature	T _{STG}	-65, +150	°C	
Thermal Resistance, Junction to Case (packaged)	R _{θJC}		°C/W	
Thermal Resistance, Junction to Case (die only)	R _{θJC}		°C/W	
Mounting Temperature (30 seconds)	T _S	320	°C	30 seconds

Electrical Characteristics (Frequency = 3.5 GHz unless otherwise stated; TC = 25 °C)

Parameter	Parameter	Typical Value	Units	Conditions
DC Characteristics				
Ohmic contact resistance	RC	0.3	Ohm-mm	25°C
Maximum Drain-source current, Id @ Vd=10V, Vg=1V (1X125µm device)	I _{dmax}	1000	mA/mm	25°C
Max. trans-conductance, @ Vd=10V, Vg=-4V ~ -1V (1X125µm device)	GM_PEAK	290	mS/mm	25°C
Maximum Drain-source current, Id @ Vd=10V, Vg=1V (1X125µm device)	I _{dmax}	1000	mA/mm	25°C
RF Characteristics				
Small Signal Gain	G _{SS}	>13	dB	V _{DD} =48V, I _{DQ} =450mA
Saturated Power Output	P _{SAT}	75	W	V _{DD} =48V, I _{DQ} =450mA
Drain Efficiency	η	>60	%	V _{DD} =48V, I _{DQ} =450mA
Intermodulation Distortion	IM3	<-30	dBc	V _{DD} =48V, I _{DQ} =450mA
Output Mismatch Stress	VSWR	10:1	ψ	



DIE Dimensions (units in microns)



Overall die size 3070 x 870 (+0/-50) microns, die thickness 100 (+/- 10) microns.
All Gate and Drain pads must be wire bonded for electrical connection.

Assembly Notes:

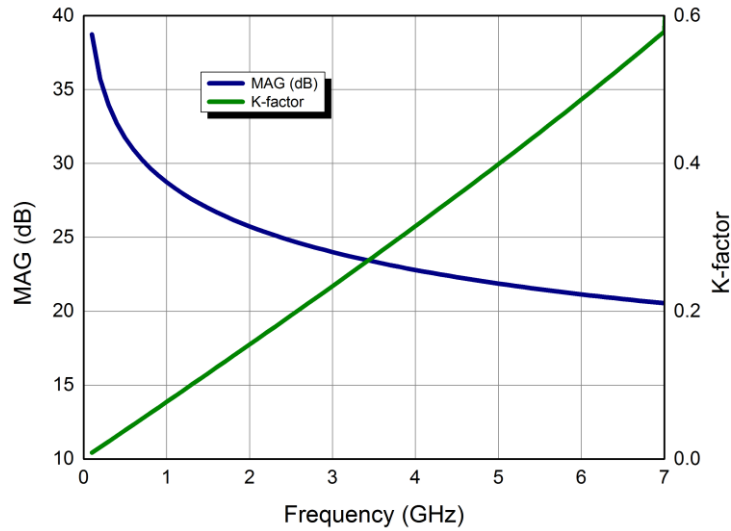
- Recommended solder is AuSn (80/20) solder. Refer to Wavepia's guide for the Eutectic Die Bond Procedure
- Vacuum collet is the preferred method of pick-up.
- The backside of the die is the Source (ground) contact.
- Die back side gold plating is 5 microns thick minimum.
- Thermosonic ball or wedge bonding are the preferred connection methods.
- Gold wire must be used for connections.



Typical Performance

Simulated Maximum Available Gain (MAG) and K Factor of the WP48007070

$V_{DD} = 48 \text{ V}$, $I_{DQ} = 450 \text{ mA}$

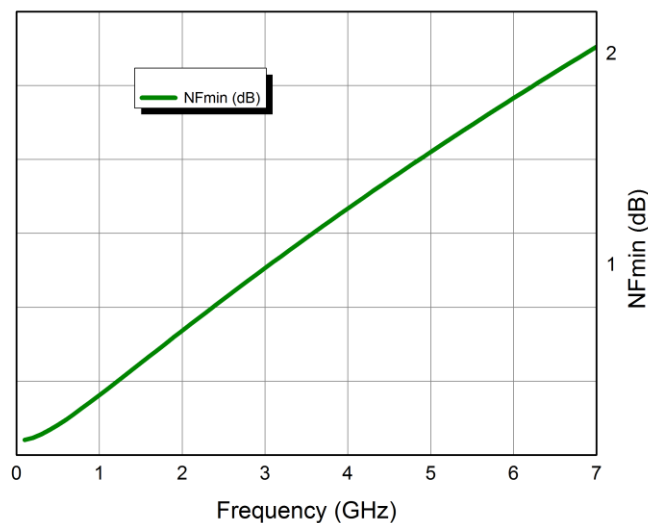


Intrinsic die parameters - reference planes at centers of gate and drain bonding pads. No wire bonds assumed.

Typical Performance

Simulated Minimum Noise Figure of the WP48007070

$V_{DD} = 48 \text{ V}$, $I_{DQ} = 450 \text{ mA}$





Typical Die S-Parameters

(Small Signal, $V_{DS} = 48\text{ V}$, $I_{DQ} = 450\text{ mA}$, magnitude / angle)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
100MHz	0.965666	-103.347	57.93143	126.1001	0.007761	36.21454	0.507722	-150.652
200MHz	0.952597	-136.79	34.06968	108.1486	0.009128	18.37754	0.592949	-161.971
300MHz	0.949065	-150.335	23.53849	100.071	0.009459	10.41444	0.615511	-166.376
400MHz	0.947827	-157.443	17.86247	95.15514	0.00957	5.613052	0.625325	-168.382
500MHz	0.947376	-161.778	14.34743	91.60005	0.009608	2.172457	0.631407	-169.349
600MHz	0.947281	-164.682	11.96312	88.75025	0.009612	-0.56285	0.636223	-169.788
700MHz	0.947383	-166.756	10.2405	86.31414	0.009598	-2.88445	0.640644	-169.93
800MHz	0.94761	-168.307	8.937358	84.14337	0.009571	-4.94069	0.645027	-169.896
900MHz	0.947927	-169.507	7.916496	82.15497	0.009536	-6.81455	0.64953	-169.754
1000MHz	0.948314	-170.461	7.094565	80.29915	0.009493	-8.55583	0.654223	-169.546
1100MHz	0.948759	-171.237	6.418067	78.54437	0.009444	-10.196	0.65913	-169.299
1200MHz	0.949252	-171.879	5.851122	76.86981	0.00939	-11.756	0.664254	-169.033
1300MHz	0.949787	-172.419	5.368778	75.26125	0.009331	-13.2499	0.669584	-168.759
1400MHz	0.950358	-172.878	4.953152	73.70869	0.009268	-14.6879	0.675104	-168.487
1500MHz	0.950961	-173.274	4.591098	72.20493	0.009201	-16.077	0.680791	-168.223
1600MHz	0.95159	-173.619	4.272732	70.74466	0.00913	-17.4226	0.686622	-167.971
1700MHz	0.952243	-173.922	3.990487	69.32392	0.009057	-18.7286	0.692573	-167.735
1800MHz	0.952916	-174.19	3.738465	67.93968	0.00898	-19.9981	0.698618	-167.515
1900MHz	0.953606	-174.43	3.512004	66.58957	0.008901	-21.2334	0.704735	-167.315
2000MHz	0.954309	-174.646	3.30737	65.27172	0.008819	-22.4365	0.7109	-167.134
2100MHz	0.955023	-174.842	3.121534	63.98461	0.008735	-23.6087	0.717092	-166.973
2200MHz	0.955746	-175.02	2.952015	62.727	0.00865	-24.7514	0.723291	-166.831
2300MHz	0.956474	-175.183	2.796758	61.49782	0.008563	-25.8657	0.729478	-166.709
2400MHz	0.957205	-175.334	2.654049	60.29617	0.008474	-26.9524	0.735638	-166.605
2500MHz	0.957937	-175.474	2.522443	59.12123	0.008385	-28.0123	0.741754	-166.519
2600MHz	0.95867	-175.604	2.400715	57.9723	0.008294	-29.0462	0.747814	-166.451
2700MHz	0.959399	-175.726	2.287818	56.8487	0.008203	-30.0547	0.753804	-166.398
2800MHz	0.960125	-175.841	2.182852	55.74982	0.008111	-31.0384	0.759715	-166.361
2900MHz	0.960845	-175.949	2.085037	54.67506	0.008019	-31.998	0.765538	-166.338
3000MHz	0.961559	-176.052	1.993696	53.62388	0.007926	-32.9339	0.771264	-166.329
3100MHz	0.962264	-176.15	1.908236	52.59571	0.007833	-33.8468	0.776887	-166.332
3200MHz	0.962961	-176.243	1.828135	51.59005	0.007741	-34.7371	0.782401	-166.347
3300MHz	0.963648	-176.332	1.752932	50.60636	0.007648	-35.6053	0.787803	-166.372
3400MHz	0.964325	-176.417	1.68222	49.64414	0.007556	-36.4521	0.793087	-166.408
3500MHz	0.96499	-176.499	1.615635	48.70289	0.007464	-37.2778	0.798252	-166.452
3600MHz	0.965643	-176.579	1.552851	47.78211	0.007373	-38.0829	0.803297	-166.505
3700MHz	0.966285	-176.655	1.493578	46.88131	0.007282	-38.868	0.808218	-166.565
3800MHz	0.966914	-176.729	1.437551	46	0.007191	-39.6336	0.813016	-166.632
3900MHz	0.96753	-176.801	1.384535	45.13771	0.007102	-40.3801	0.817692	-166.705

Disclaimer

Information furnished by WAVEPIA Co., Ltd. is believed to be accurate and reliable. However, no responsibility is assumed by WAVEPIA Co., Ltd. for its use, nor for any infringements of patents or other rights of third parties that may result from its use. The information contained is provided “as it is” and with all defects, and the whole risk associated with such information is entirely with the user. Specifications subject to change without notice. WAVEPIA Co., Ltd. and registered trademarks are the property of their respective owners. Customers must search and verify the updated information before placing orders for our products. We makes no guarantee or representation regarding the information contained herein the using of products for any specific purpose. WAVEPIA Co., Ltd. products are not warranted or authorized for use as key components in conditions, or other applications where a failure would be expected to cause severe personal injury or death.

For more information, please contact :

- *For more details : WAVEPIA Co., Ltd.*
- *#1301, 557, Dongtangiheung-ro, Hwaseong-si, Gyeonggi-do, Republic of Korea*
- *Application Support: platune@wavepia.com*

Sanghun Lee
CTO
WAVEPIA, IC DESIGN
+82.31.8058.3374